

HIGH-POWER PNP SILICON TRANSISTORS

... designed for use in industrial power amplifiers and switching circuit applications.

FEATURES:

- * High DC Current Gain
 $h_{FE} = 20-80 @ I_C = 10A$
 $= 12 \text{ (Min)} @ I_C = 25A$
- * Low Collector-Emitter Saturation Voltage
 $V_{CE(SAT)} = 1.0V \text{ (Max.)} @ I_C = 10 A, I_B = 1.0A$
- * Complement to 2N6338 thru 2N6340

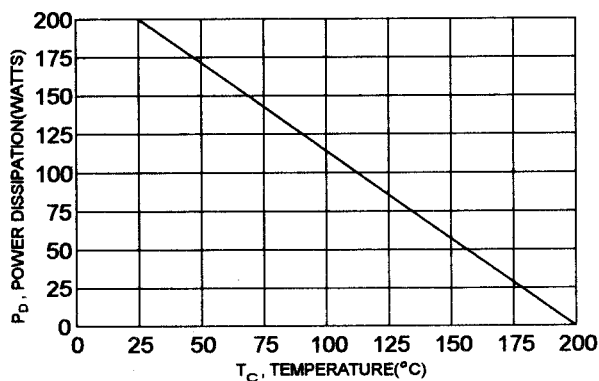
MAXIMUM RATINGS

Characteristic	Symbol	2N6436	2N6437	2N6438	Unit
Collector-Emitter Voltage	V_{CEO}	80	100	120	V
Collector-Base Voltage	V_{CBO}	100	120	140	V
Emitter-Base Voltage	V_{EBO}	6.0			V
Collector Current-Continuous -Peak	I_C	25 50			A
Base Current	I_B	10			A
Total Power Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	200 1.14			W W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-65 to +200			$^\circ C$

THERMAL CHARACTERISTICS

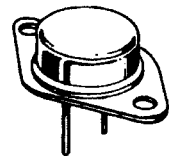
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.875	$^\circ C/W$

FIGURE -1 POWER DERATING

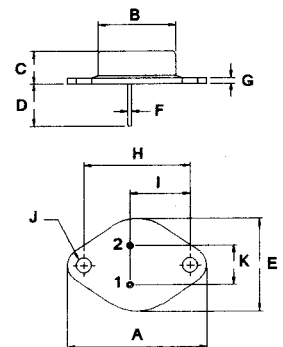


PNP
2N6436
2N6437
2N6438

25 AMPERE
 POWER TRANSISTOR
 PNP SILICON
 80-120 VOLTS
 200 WATTS



TO-3



PIN 1. BASE
 2. EMITTER
 COLLECTOR (CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector -Emitter Sustaining Voltage (1) ($I_C = 50 \text{ mA}$, $I_B = 0$)	2N6436 2N6437 2N6438	$V_{CE(sus)}$	80 100 120	V
Collector Cutoff Current ($V_{CE} = 40 \text{ V}$, $I_B = 0$) ($V_{CE} = 50 \text{ V}$, $I_B = 0$) ($V_{CE} = 60 \text{ V}$, $I_B = 0$)	2N6436 2N6437 2N6438	I_{CEO}	50 50 50	μA
Collector Cutoff Current ($V_{CB} = \text{Rated } V_{CB}$, $I_E = 0$)		I_{CBO}	10	μA
Emitter Cutoff Current ($V_{EB} = 6.0 \text{ V}$, $I_C = 0$)		I_{EBO}	100	μA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 0.5 \text{ A}$, $V_{CE} = 2.0 \text{ V}$) ($I_C = 10 \text{ A}$, $V_{CE} = 2.0 \text{ V}$) ($I_C = 25 \text{ A}$, $V_{CE} = 2.0 \text{ V}$)		hFE	30 20 12	80
Collector-Emitter Saturation Voltage ($I_C = 10 \text{ A}$, $I_B = 1.0 \text{ A}$) ($I_C = 25 \text{ A}$, $I_B = 2.5 \text{ A}$)		$V_{CE(sat)}$	1.0 1.8	V
Base-Emitter Saturation Voltage ($I_C = 10 \text{ A}$, $I_B = 1.0 \text{ A}$) ($I_C = 25 \text{ A}$, $I_B = 2.5 \text{ A}$)		$V_{BE(sat)}$	1.8 2.5	V

DYNAMIC CHARACTERISTICS

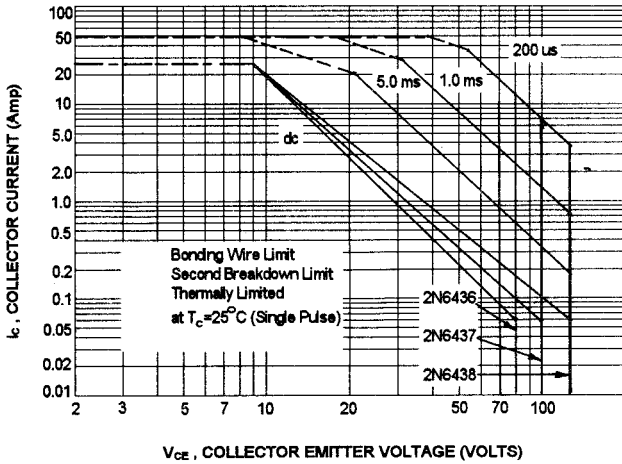
Current-Gain Bandwidth Product (2) ($I_C = 1.0 \text{ A}$, $V_{CE} = 10 \text{ V}$, $f = 10 \text{ MHz}$)		f_T	40	MHz
Output Capacitance ($V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 0.1 \text{ MHz}$)		C_{ob}	700	pF

SWITCHING CHARACTERISTICS

Rise Time	$V_{CC} = 80 \text{ V}$, $I_C = 10 \text{ A}$ $I_{B1} = -I_{B2} = 1.0 \text{ A}$, $V_{BE(off)} = 6.0 \text{ V}$	t_r	0.3	μs
Storage Time		t_s	2.0	μs
Fall Time		t_f	0.4	μs

(1) Pulse Test: Pulse width = 300 μs , Duty Cycle $\leq 2.0\%$ (2) $f_T = |h_{fe}| \cdot f_{test}$

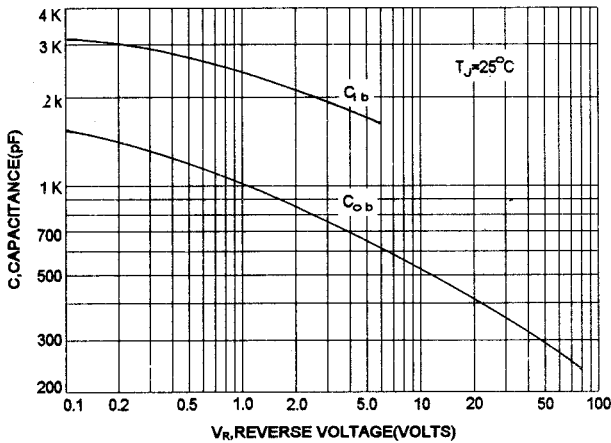
ACTIVE-REGION SAFE OPERATING AREA (SOA)



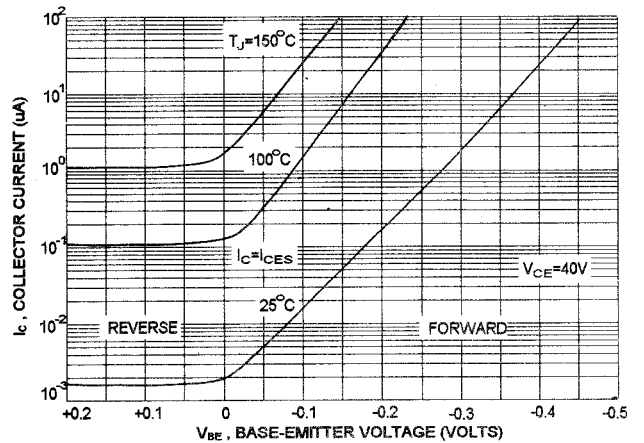
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on $T_{J(PK)} = 200^\circ\text{C}$; T_C is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(PK)} \leq 200^\circ\text{C}$. At high case temperatures, thermal limitation will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

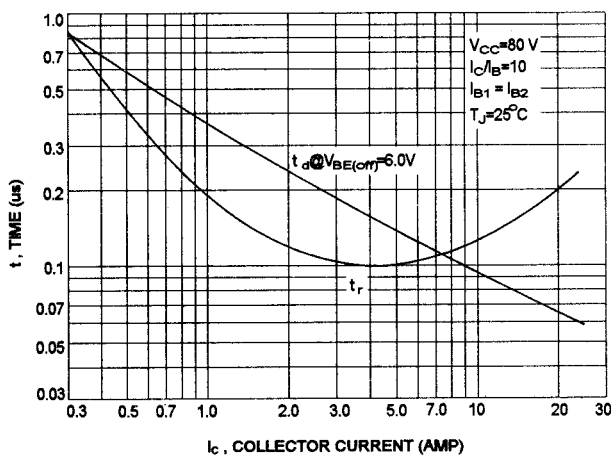
CAPACITANCES



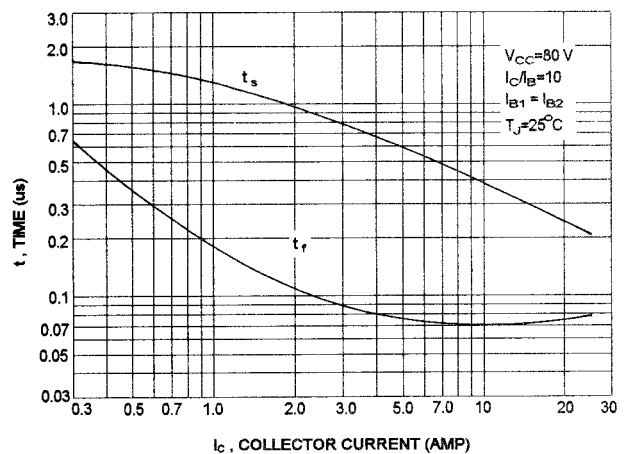
COLLECTOR CUT-OFF REGION



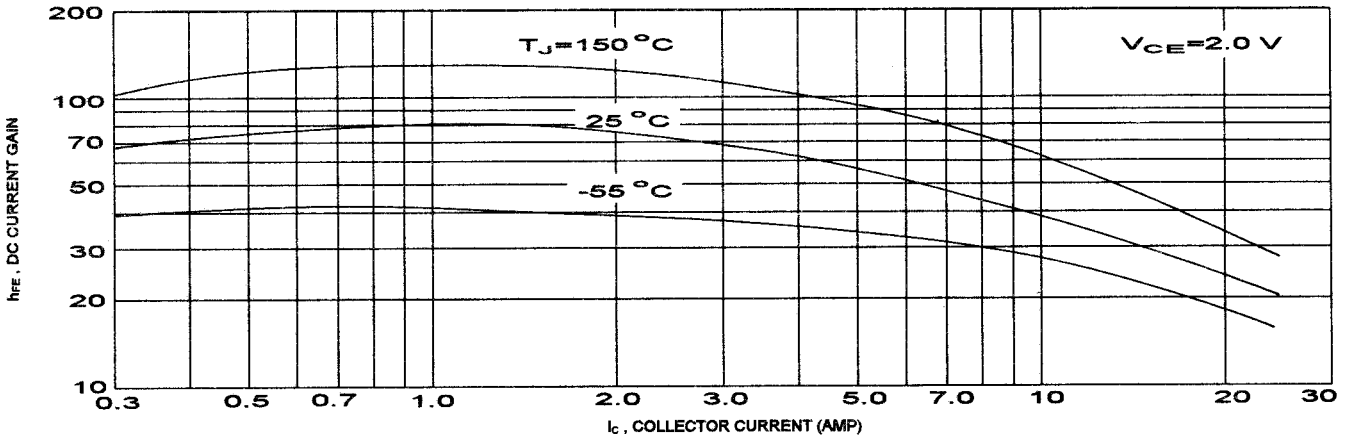
TURN-ON TIME



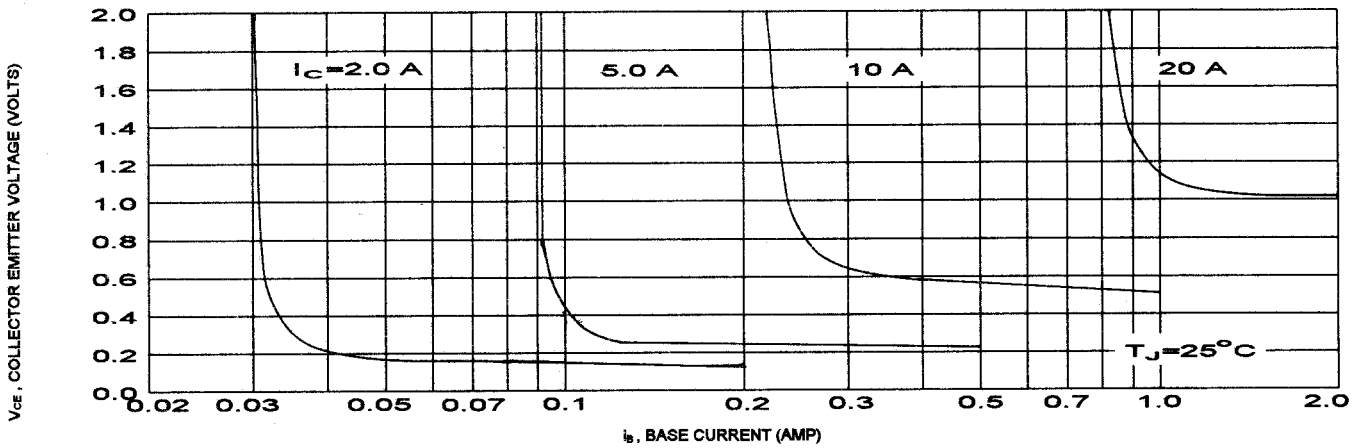
TURN-OFF TIME



DC CURRENT GAIN



COLLECTOR SATURATION REGION



"ON" VOLTAGES

